40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
40V	6mΩ @ V_{GS} = 10V	140A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

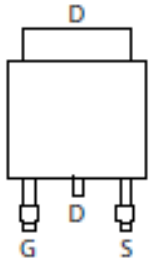
Features

- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH4006SK3Q)**

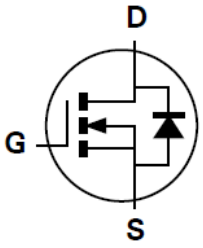
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.315 grams (Approximate)

Top View



Pin Out Top View



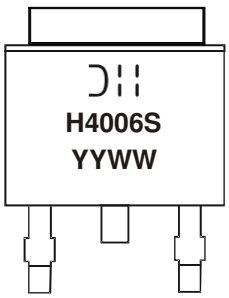
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH4006SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



=Manufacturer's Marking
H4006S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	T_A = +25°C T_A = +70°C	I_D	20 16	A
Continuous Drain Current (Note 7) V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	140 100	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)		I_{DM}	200	A
Maximum Continuous Body Diode Forward Current (Note 7)		I_S	120	A
Avalanche Current, L = 0.1mH (Note 8)		I_{AS}	64	A
Avalanche Energy, L = 0.1mH (Note 8)		E_{AS}	208	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	68	°C/W
	t<10s		29	
Total Power Dissipation (Note 6)		P_D	3.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	42	°C/W
	t<10s		21	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	0.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current, T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	6	mΩ	V_{GS} = 10V, I_D = 86A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1.0A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	2,280	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	556	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	282	—	pF	
Gate Resistance	R_g	—	1.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 6V)	Q_g	—	32	—	nC	V_{DS} = 32V, I_D = 86A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	51	—	nC	
Gate-Source Charge	Q_{gs}	—	9.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	20.4	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	7.7	—	ns	V_{GS} = 10V, V_{DS} = 20V, R_G = 3.5Ω, I_D = 86A
Turn-On Rise Time	t_R	—	9.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	18	—	ns	
Turn-Off Fall Time	t_F	—	8.1	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	32	—	ns	I_F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	28	—	nC	I_F = 50A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

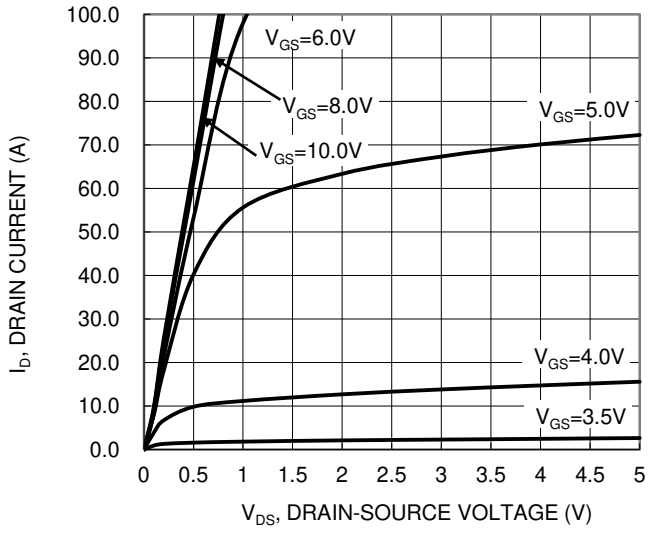


Figure 1. Typical Output Characteristic

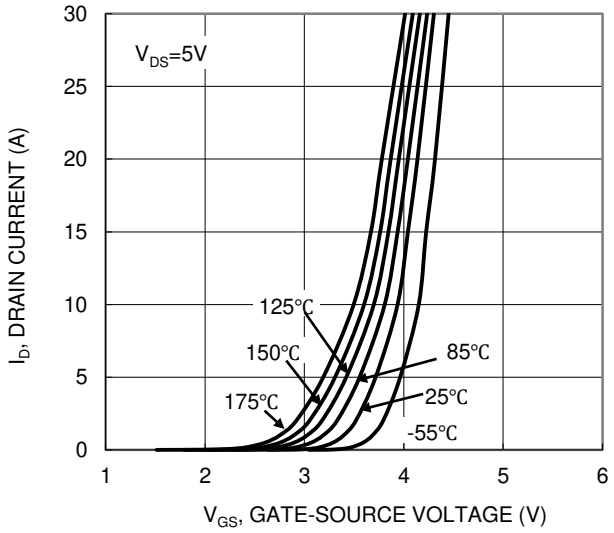


Figure 2. Typical Transfer Characteristic

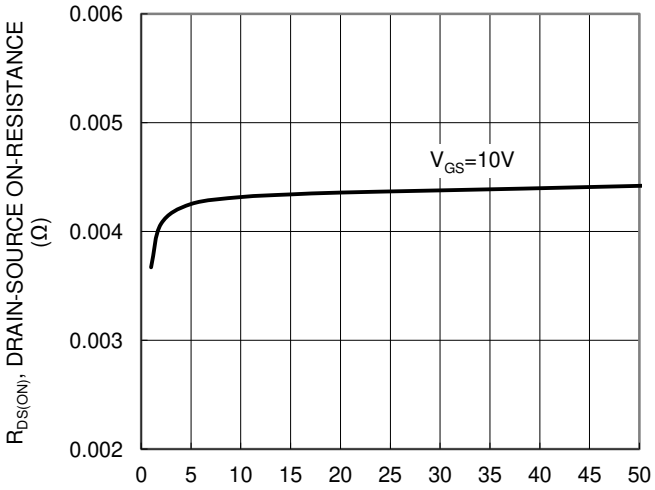


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

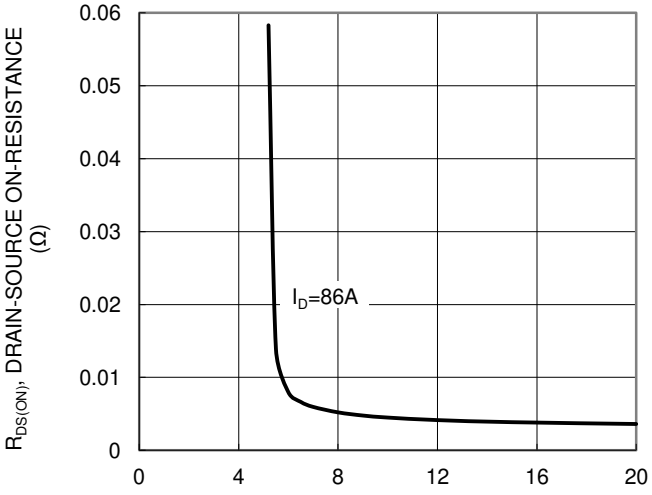


Figure 4. Typical Transfer Characteristic

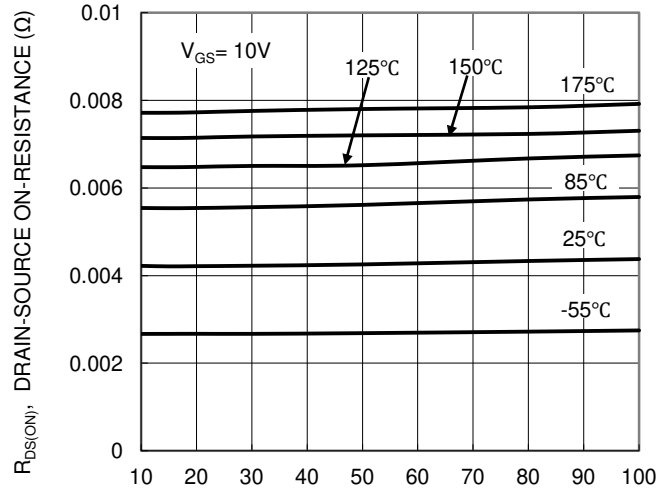


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

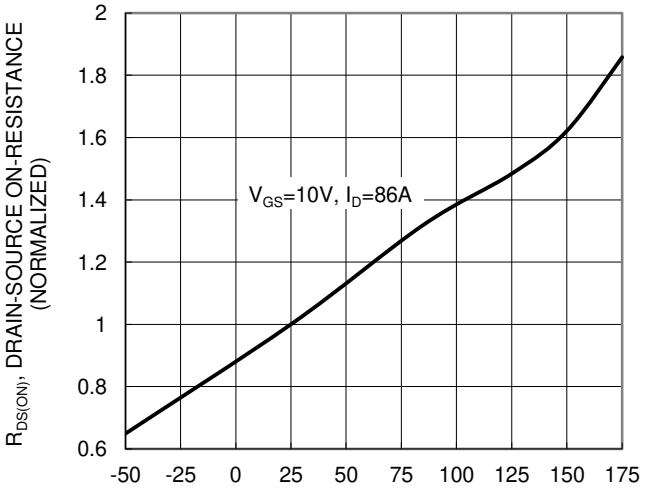


Figure 6. On-Resistance Variation with Junction Temperature

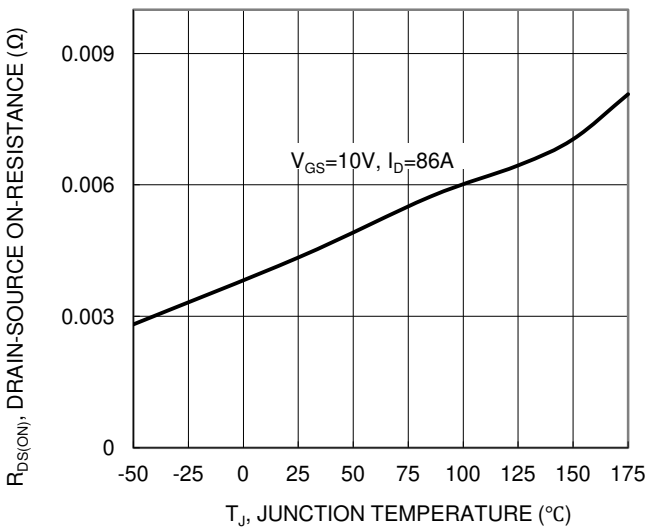


Figure 7. On-Resistance Variation with Junction Temperature

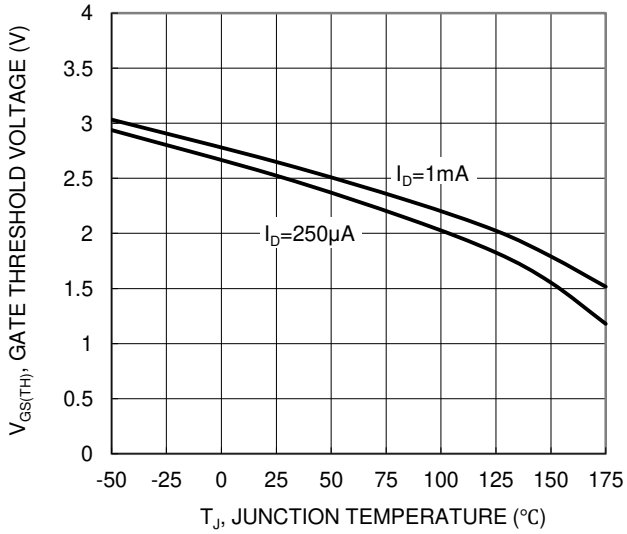


Figure 8. Gate Threshold Variation vs. Junction Temperature

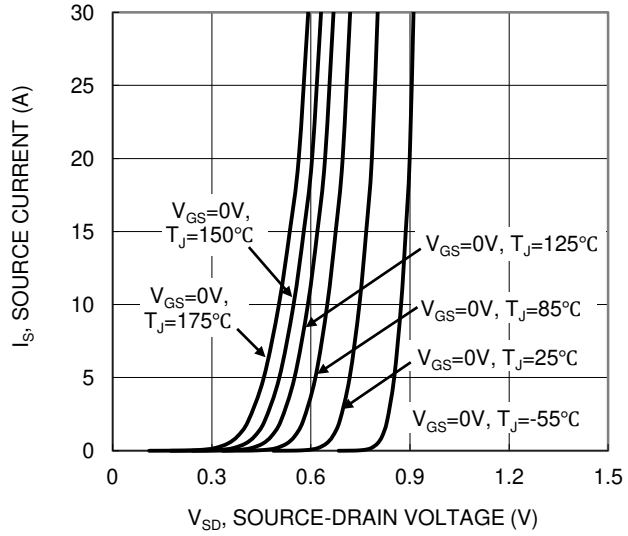


Figure 9. Diode Forward Voltage vs. Current

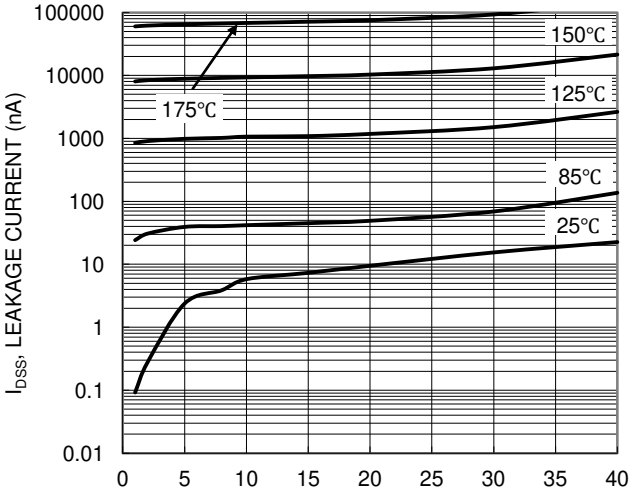


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

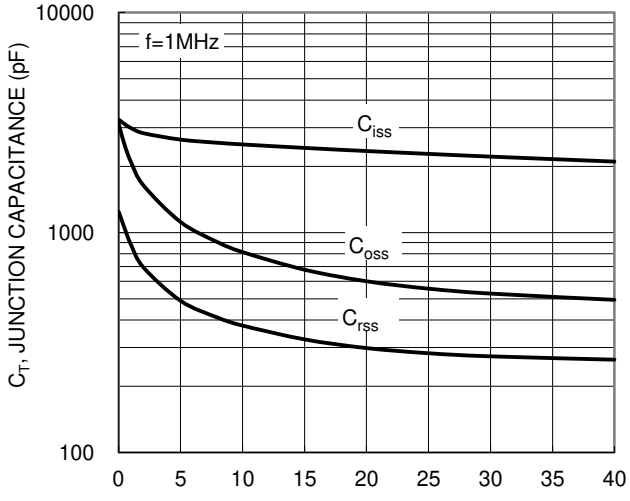


Figure 11. Typical Junction Capacitance

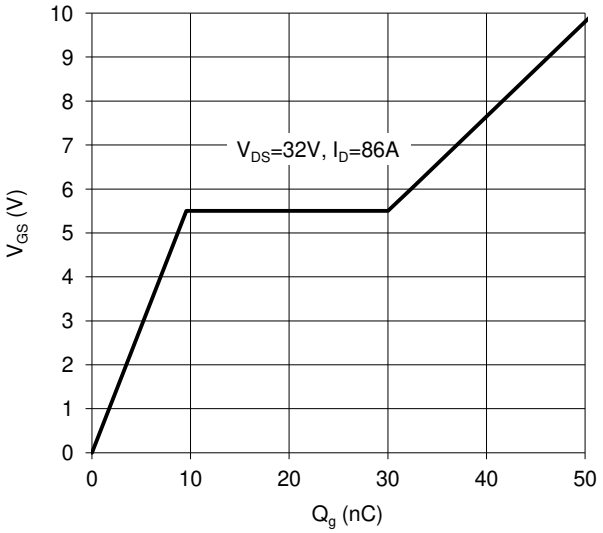


Figure 12. Gate Charge

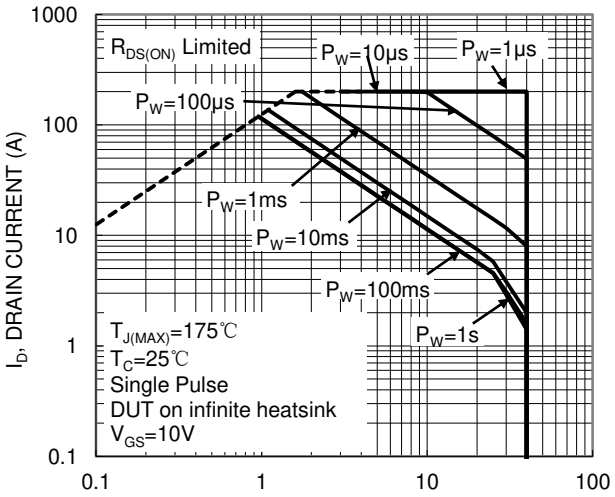


Figure 13. SOA, Safe Operation Area

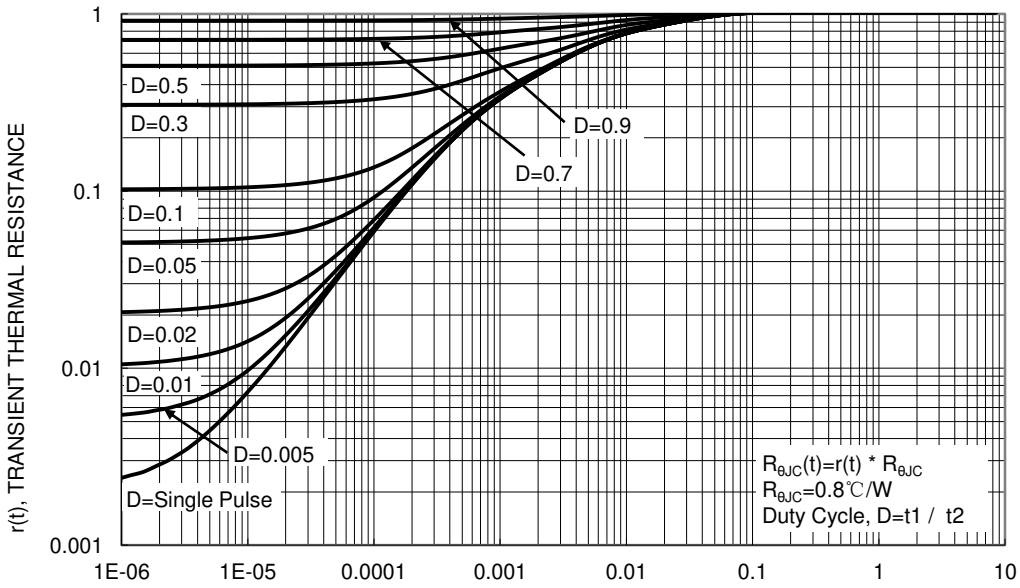
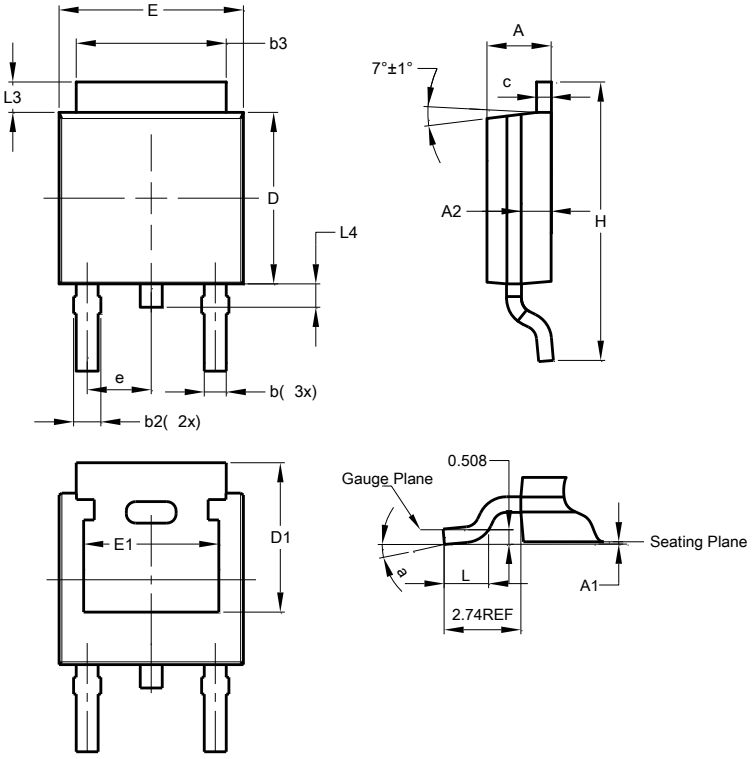


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

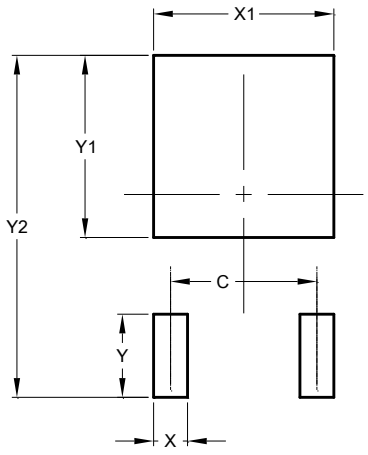
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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